P-Channel 20-V (D-S) MOSFET

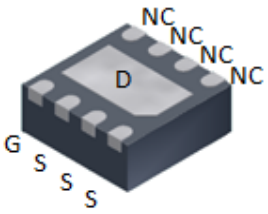
Key Features:
- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- 2mm x 2mm footprint DFN package
- RDS rated at 1.8V Gate-drive

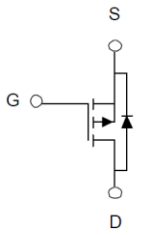
PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (mΩ)	I_D(A)
-20	42 @ V_{GS} = -4.5V	-6.6
	57 @ V_{GS} = -2.5V	-5.7
	86 @ V_{GS} = -1.8V	-1

Typical Applications:
- Battery Powered Instruments
- Portable Computing
- Mobile Phones
- GPS Units and Media Players

Pb-free
RoHS COMPLIANT
HALOGEN FREE

DFN2x2-8





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)				
Parameter		**Symbol**	**Limit**	**Units**
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	±8	
Continuous Drain Current [a]	T_A=25°C	I_D	-6.6	A
	T_A=70°C		-5.3	
Pulsed Drain Current [b]		I_{DM}	-20	
Continuous Source Current (Diode Conduction) [a]		I_S	4	A
Power Dissipation [a]	T_A=25°C	P_D	3	W
	T_A=70°C		1.92	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS				
Parameter		**Symbol**	**Maximum**	**Units**
Maximum Junction-to-Ambient [a]	t <= 5 sec	$R_{\theta JA}$	40	°C/W
	Steady State		90	

Notes
a. Surface Mounted on 1” x 1” FR4 Board.
b. Pulse width limited by maximum junction temperature

Electrical Characteristics

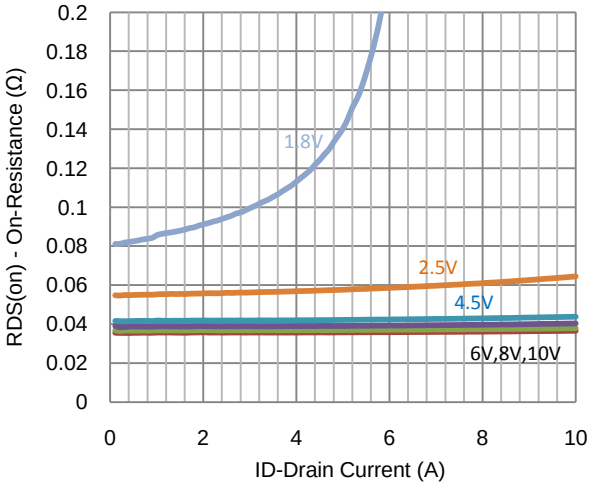
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250 uA	-0.4			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = -8 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -16 V, V_{GS} = 0 V			1	uA
		V_{DS} = -16 V, V_{GS} = 0 V, T_J = 55°C			25	
On-State Drain Current	$I_{D(on)}$	V_{DS} = -5 V, V_{GS} = -4.5 V	-10			A
Drain-Source On-Resistance	$r_{DS(on)}$	V_{GS} = -4.5 V, I_D = -4.4 A			42	mΩ
		V_{GS} = -2.5 V, I_D = -3.6 A			57	
		V_{GS} = -1.8 V, I_D = -1 A			86	
Forward Transconductance	g_{fs}	V_{DS} = -15 V, I_D = -4.4 A		20		S
Diode Forward Voltage	V_{SD}	I_S = -2 A, V_{GS} = 0 V		0.83		V
Dynamic						
Total Gate Charge	Q_g	V_{DS} = -10 V, V_{GS} = -4.5 V, I_D = -4.4 A		6.8		nC
Gate-Source Charge	Q_{gs}			1.8		
Gate-Drain Charge	Q_{gd}			2.3		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = -10 V, R_L = 2.3 Ω, I_D = -4.4 A, V_{GEN} = -4.5 V, R_{GEN} = 6 Ω		6		ns
Rise Time	t_r			6		
Turn-Off Delay Time	$t_{d(off)}$			23		
Fall Time	t_f			15		
Input Capacitance	C_{iss}	V_{DS} = -15 V, V_{GS} = 0 V, f = 1 MHz		837		pF
Output Capacitance	C_{oss}			98		
Reverse Transfer Capacitance	C_{rss}			75		
Gate Resistance	R_g	f = 1 MHz		3.7		Ω

Notes

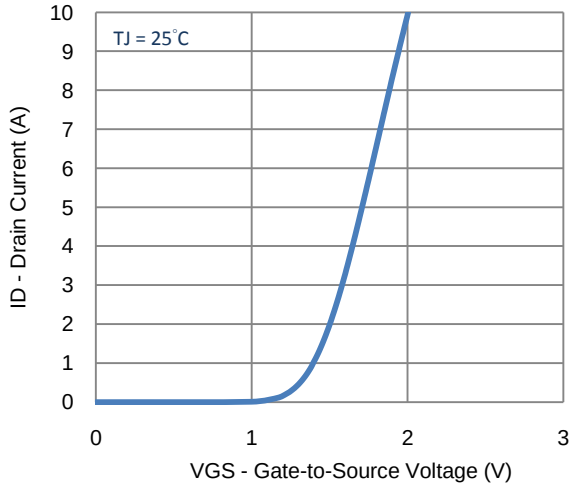
a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.

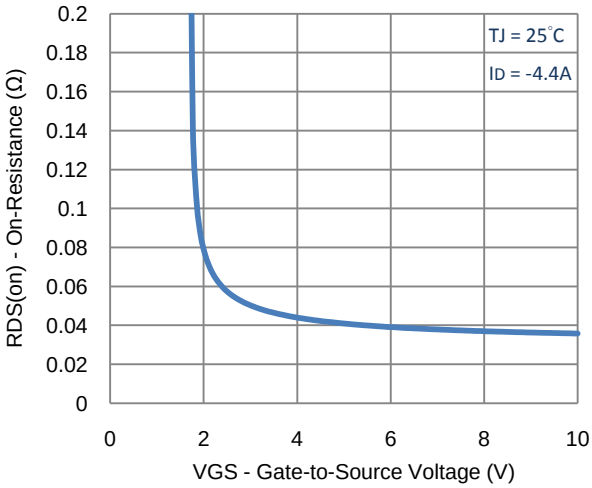
Typical Electrical Characteristics



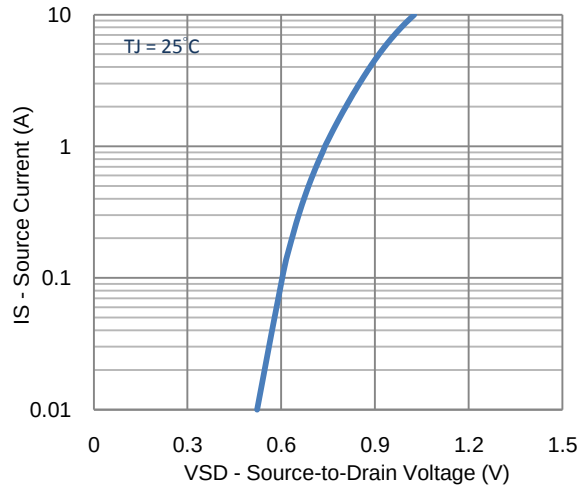
1. On-Resistance vs. Drain Current



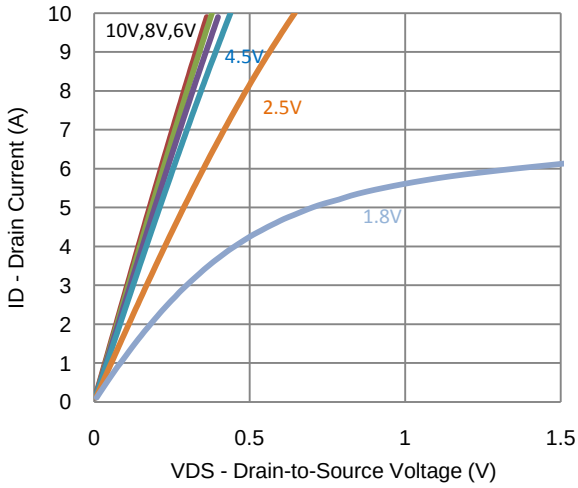
2. Transfer Characteristics



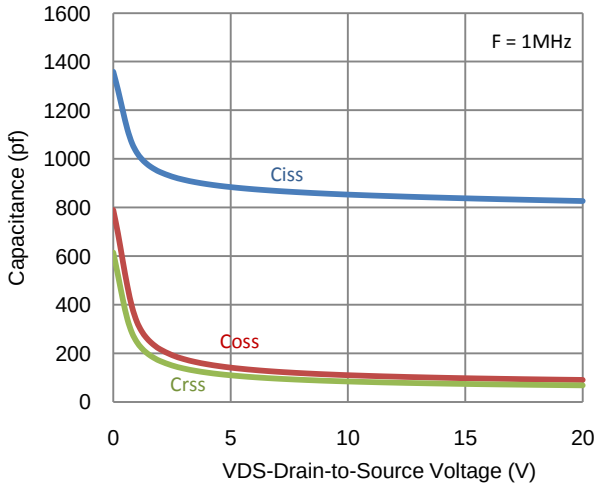
3. On-Resistance vs. Gate-to-Source Voltage



4. Drain-to-Source Forward Voltage

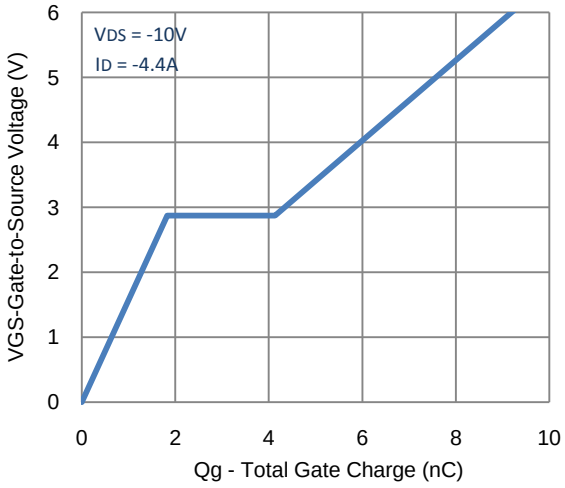


5. Output Characteristics

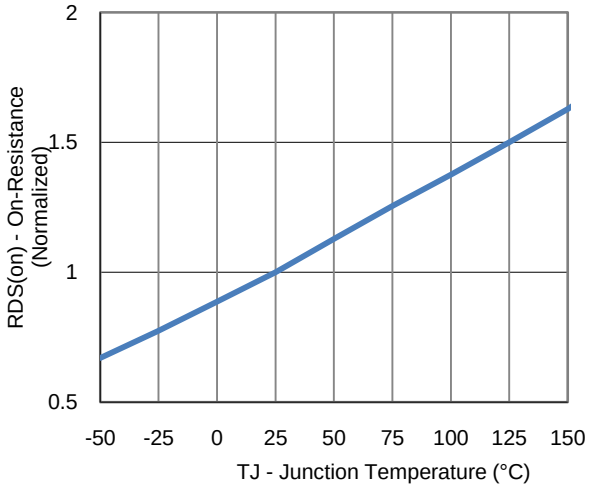


6. Capacitance

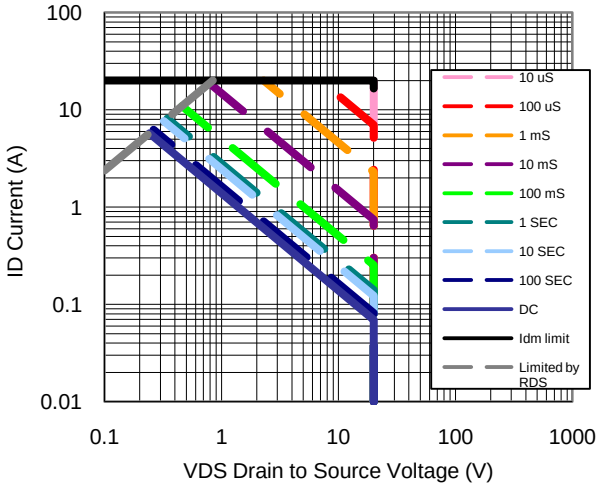
Typical Electrical Characteristics



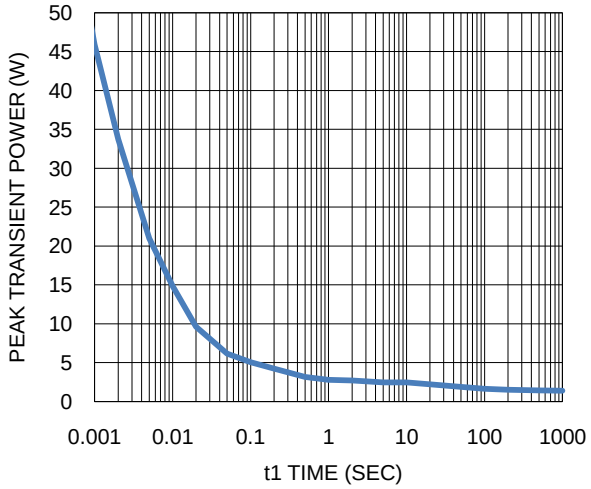
7. Gate Charge



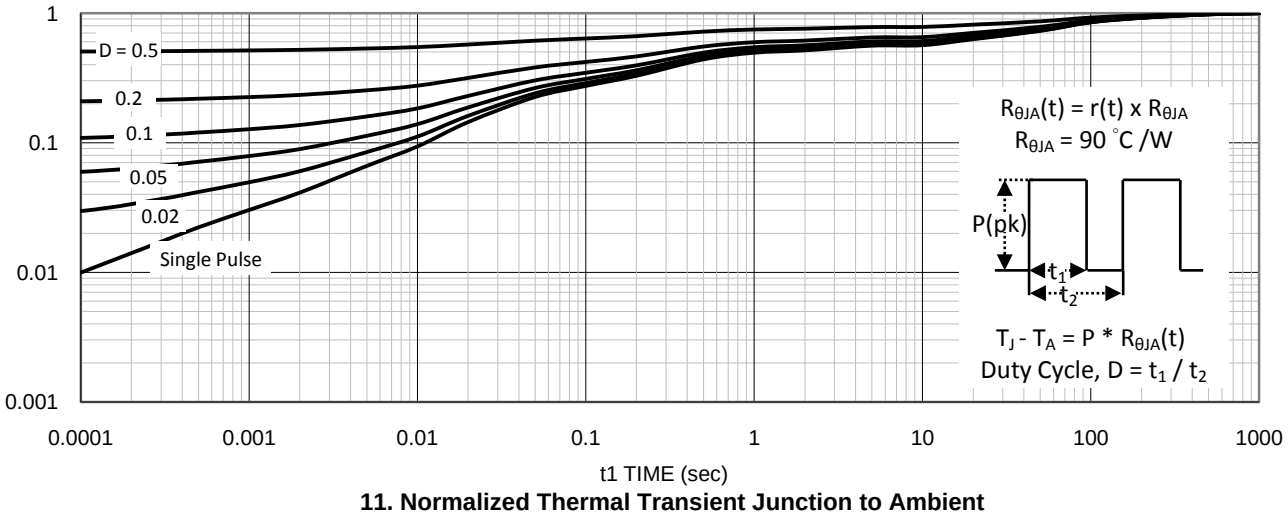
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area

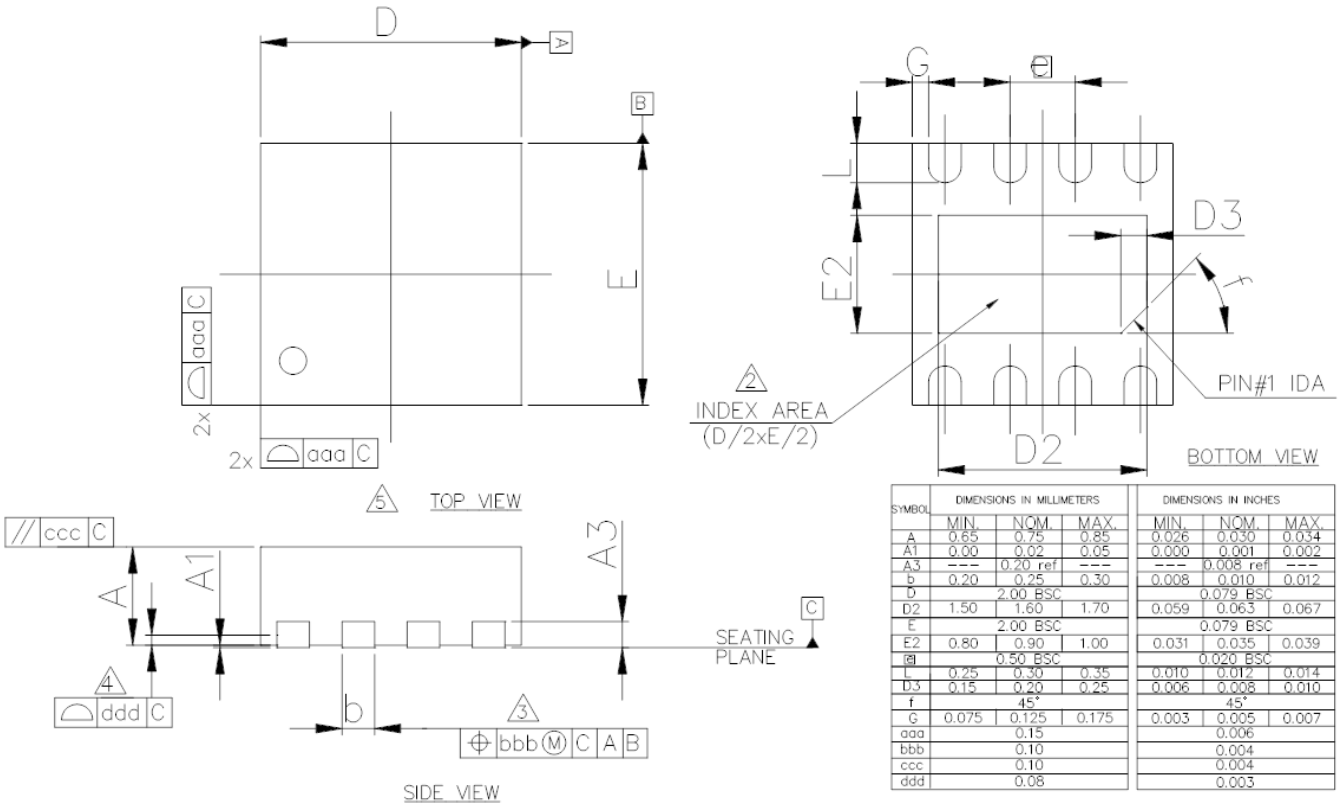


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOL	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.65	0.75	0.85	0.026	0.030	0.034
A1	0.00	0.02	0.05	0.000	0.001	0.002
A3	---	0.20 ref	---	---	0.008 ref	---
b	0.20	0.25	0.30	0.008	0.010	0.012
D		2.00 BSC			0.079 BSC	
D2	1.50	1.60	1.70	0.059	0.063	0.067
E		2.00 BSC			0.079 BSC	
E2	0.80	0.90	1.00	0.031	0.035	0.039
e		0.50 BSC			0.020 BSC	
L	0.25	0.30	0.35	0.010	0.012	0.014
D3	0.15	0.20	0.25	0.006	0.008	0.010
f		45°			45°	
G	0.075	0.125	0.175	0.003	0.005	0.007
aaa		0.15			0.006	
bbb		0.10			0.004	
ccc		0.10			0.004	
ddd		0.08			0.003	